

MOS FIELD EFFECT TRANSISTOR  
2SJ449

SWITCHING  
P-CHANNEL MOS FET  
INDUSTRIAL USE

DESCRIPTION

The 2SJ449 is P-Channel MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

- Low On-Resistance  
 $R_{DS(on)} = 0.8 \Omega \text{ MAX. (@ } V_{GS} = -10 \text{ V, } I_D = -3.0 \text{ A)}$
- Low  $C_{iss}$   $C_{iss} = 1040 \text{ pF TYP.}$
- High Avalanche Capability Ratings
- Isolated TO-220 Package

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25 \text{ }^\circ\text{C}$ )

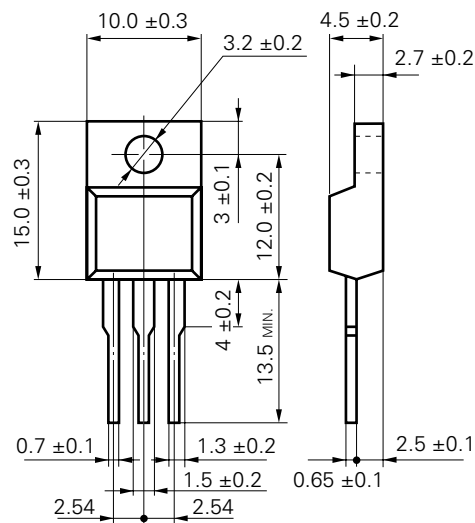
Drain to Source Voltage	$V_{DSS}$	-250	V
Gate to Source Voltage	$V_{GSS}$	$\mp 30$	V
Drain Current (DC)	$I_{D(DC)}$	$\mp 6.0$	A
Drain Current (pulse)*	$I_{D(pulse)}$	$\mp 24$	A
Total Power Dissipation ( $T_c = 25 \text{ }^\circ\text{C}$ )	$P_{T1}$	35	W
Total Power Dissipation ( $T_A = 25 \text{ }^\circ\text{C}$ )	$P_{T2}$	2.0	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Avalanche Current**	$I_{AS}$	-6.0	A
Single Avalanche Energy**	$E_{AS}$	180	mJ

\*  $PW \leq 10 \mu s$ , Duty Cycle  $\leq 1 \%$

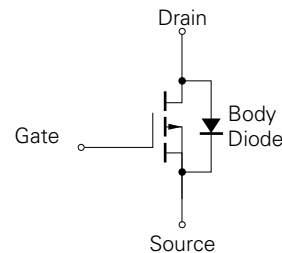
\*\* Starting  $T_{ch} = 25 \text{ }^\circ\text{C}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = -20 \text{ V} \rightarrow 0$

PACKAGE DIMENSIONS

(in millimeters)



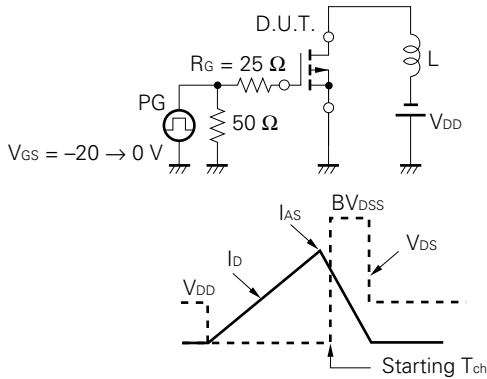
MP-45F (ISOLATED TO-220)



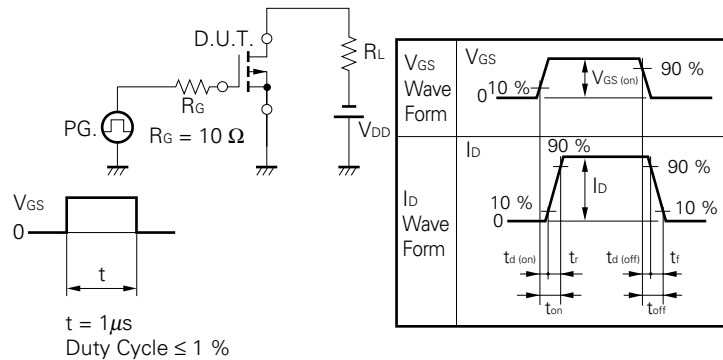
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-Resistance	R <sub>DS(on)</sub>		0.55	0.8	Ω	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.0 A
Gate to Source Cutoff Voltage	V <sub>GS(off)</sub>	-4.0	-4.8	-5.5	V	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA
Forward Transfer Admittance	y <sub>fs</sub>	2.0	3.5		S	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -3.0 A
Drain Leakage Current	I <sub>DSS</sub>			-100	μA	V <sub>DS</sub> = -250 V, V <sub>GS</sub> = 0
Gate to Source Leakage Current	I <sub>GSS</sub>			±100	nA	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0
Input Capacitance	C <sub>iss</sub>		1040		pF	V <sub>DS</sub> = -10 V
Output Capacitance	C <sub>oss</sub>		360		pF	V <sub>GS</sub> = 0
Reverse Transfer Capacitance	C <sub>rss</sub>		70		pF	f = 1 MHz
Turn-On Delay Time	t <sub>d(on)</sub>		24		ns	I <sub>D</sub> = -3.0 A
Rise Time	t <sub>r</sub>		16		ns	V <sub>GS(on)</sub> = -10 V
Turn-Off Delay Time	t <sub>d(off)</sub>		47		ns	V <sub>DD</sub> = -125 V
Fall Time	t <sub>f</sub>		14		ns	R <sub>G</sub> = 10 Ω, R <sub>L</sub> = 42 Ω
Total Gate Charge	Q <sub>G</sub>		23.1		nC	I <sub>D</sub> = -6.0 A
Gate to Source Charge	Q <sub>GS</sub>		7.1		nC	V <sub>DD</sub> = -200 V
Gate to Drain Charge	Q <sub>GD</sub>		12.9		nC	V <sub>GS</sub> = -10 V
Body Diode Forward Voltage	V <sub>F(S-D)</sub>		0.92		V	I <sub>F</sub> = -6.0 A, V <sub>GS</sub> = 0
Reverse Recovery Time	t <sub>rr</sub>		155		ns	I <sub>F</sub> = -6.0 A, V <sub>GS</sub> = 0
Reverse Recovery Charge	Q <sub>rr</sub>		930		nC	di/dt = 50 A/μs

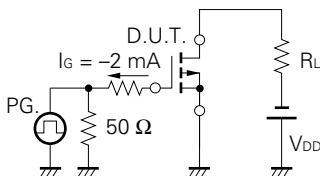
**Test Circuit 1 Avalanche Capability**



**Test Circuit 2 Switching Time**



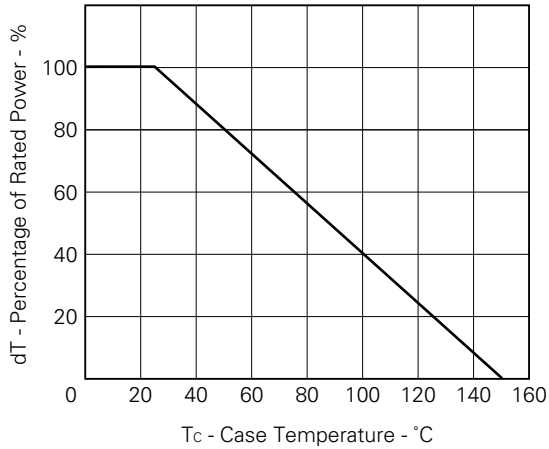
**Test Circuit 3 Gate Charge**



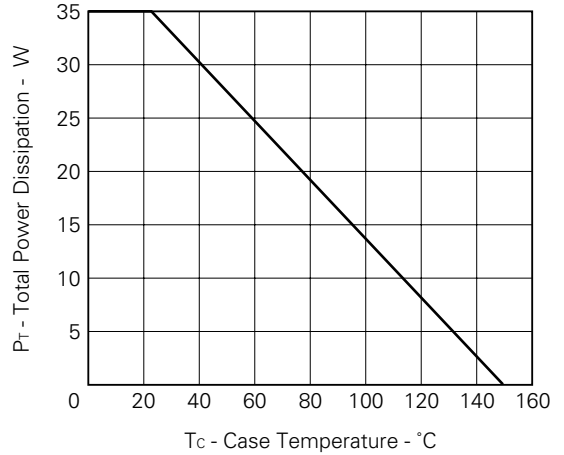
The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)

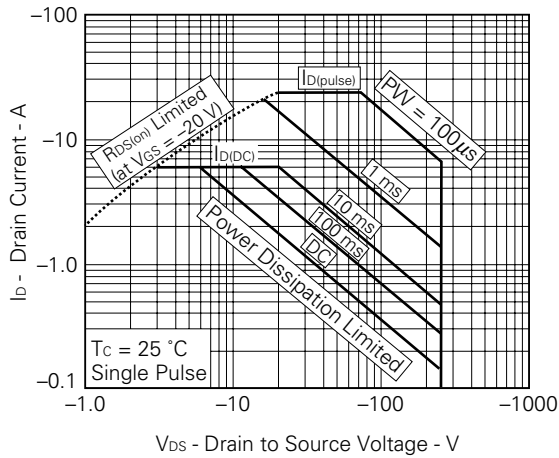
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



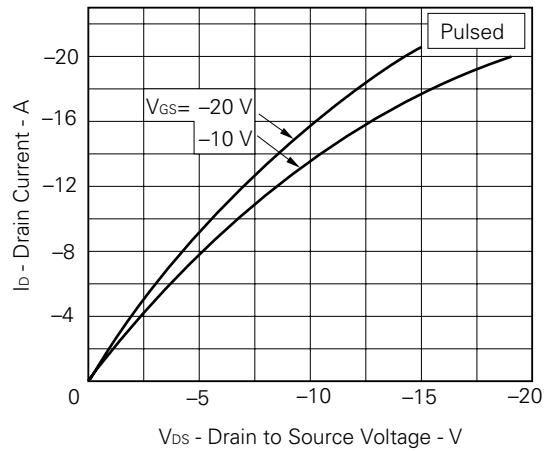
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



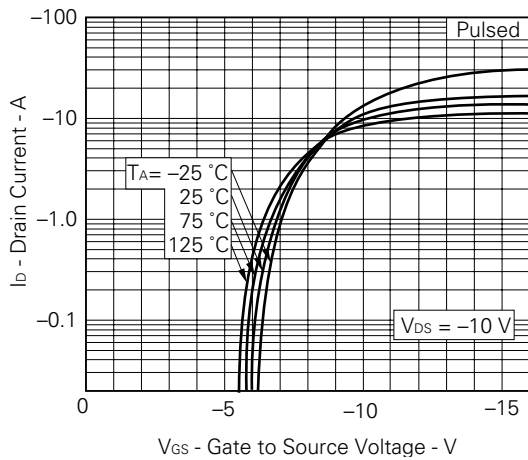
FORWARD BIAS SAFE OPERATING AREA



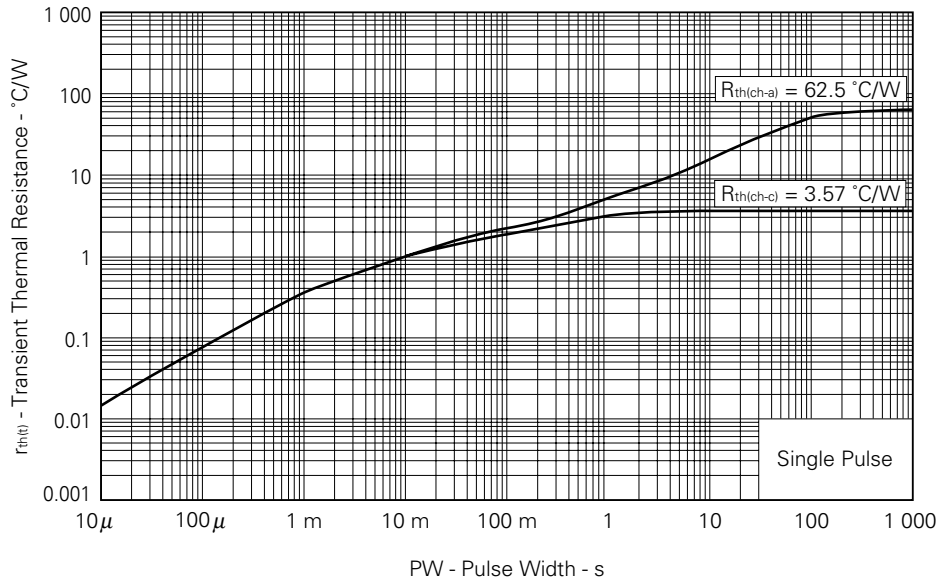
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



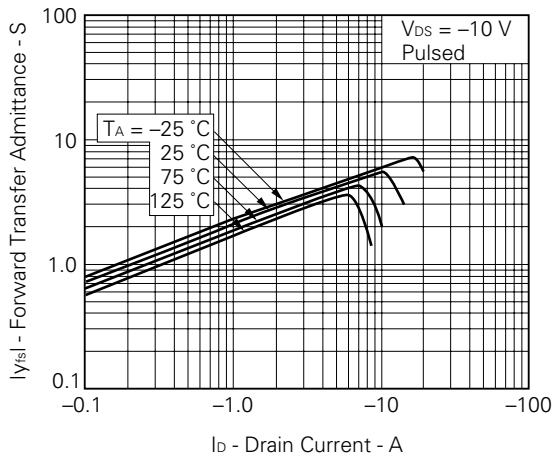
FORWARD TRANSFER CHARACTERISTICS



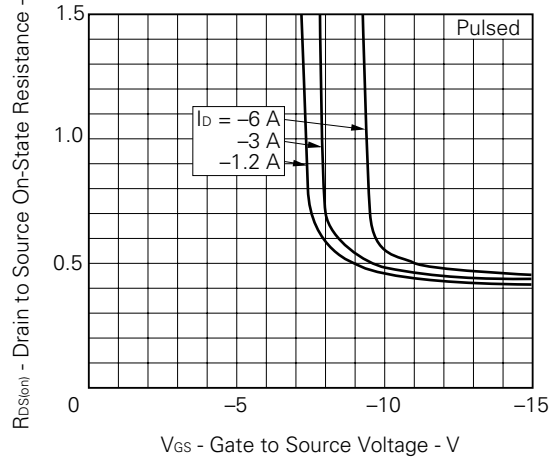
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



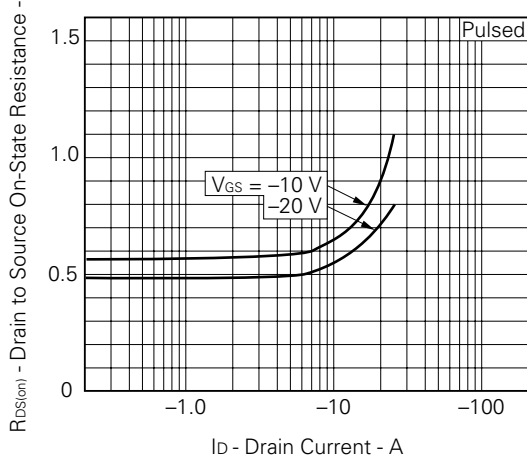
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



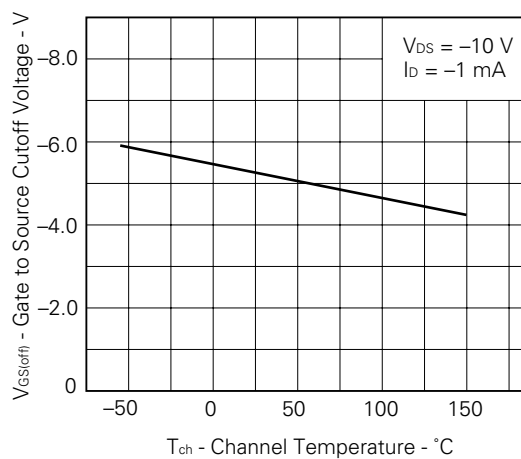
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



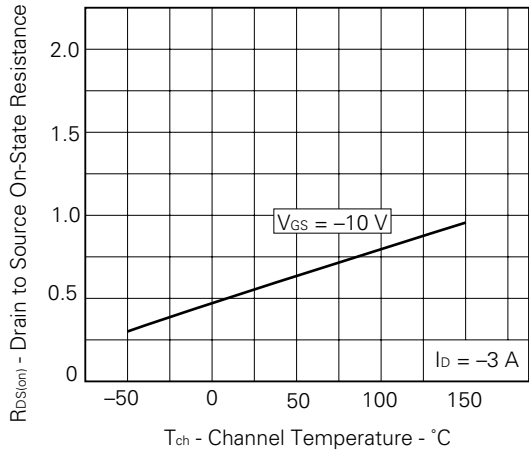
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



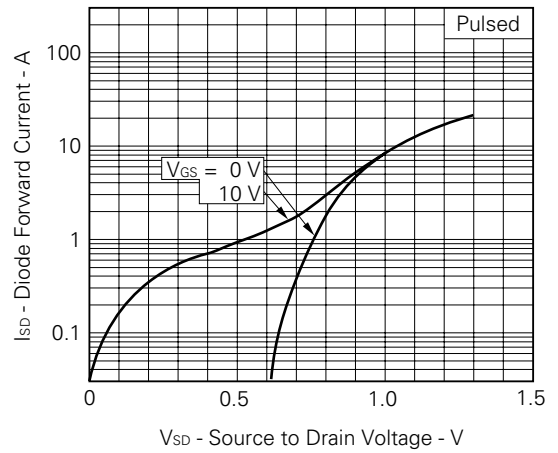
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



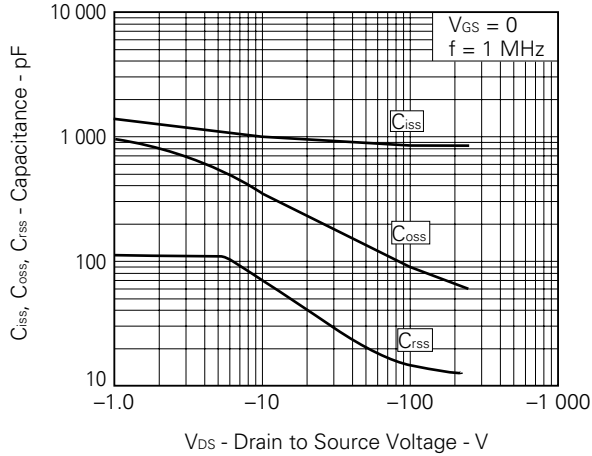
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



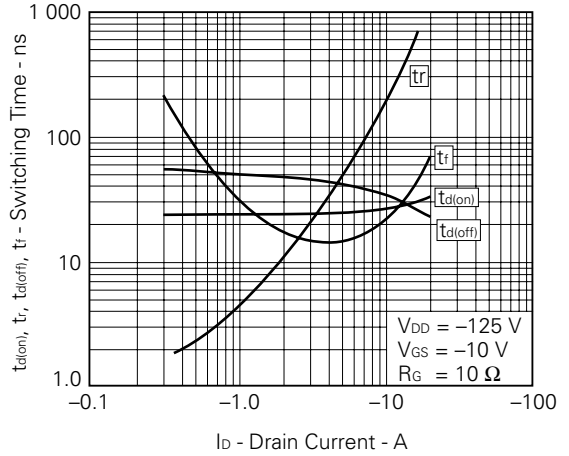
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



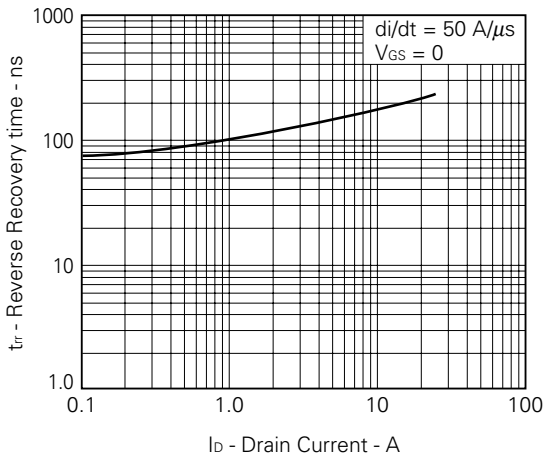
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



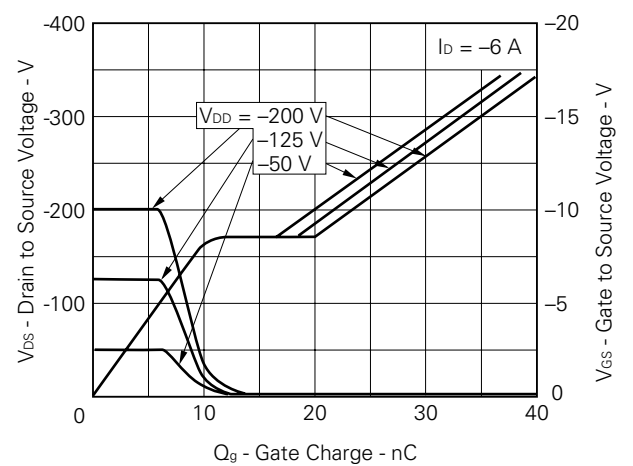
SWITCHING CHARACTERISTICS



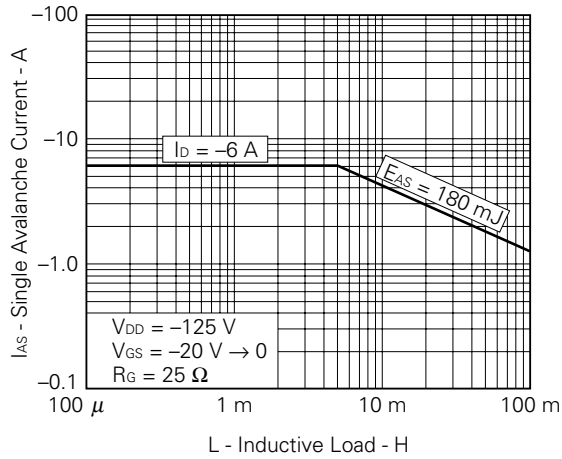
REVERSE RECOVERY TIME vs. DRAIN CURRENT



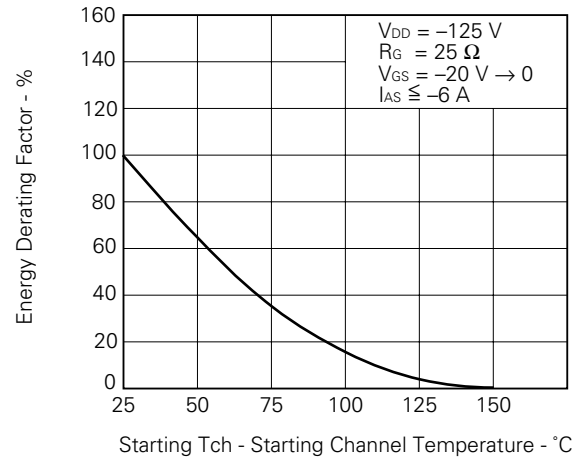
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY DERATING FACTOR



**REFERENCE**

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134
Power MOS FET features and application switching power supply.	TEA-1034
Application circuits using Power MOS FET.	TEA-1035
Safe operating area of Power MOS FET.	TEA-1037

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device is actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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Anti-radioactive design is not implemented in this product.